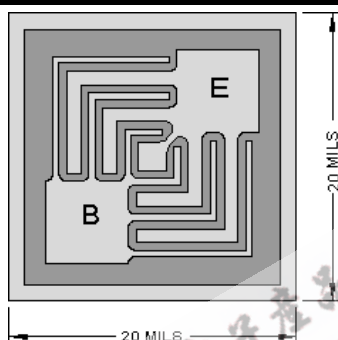


**Chip Type 2C2222A**  
**Geometry 0400**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N2219, 2N2219A, 2N2222,**  
**2N2222A**



[Request Quotation](#)

Chip type **2C2222A** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N2222A, 2N2222, 2N2219, 2N2219A, 2N2219AL,  
 2N2222AUB, SD2222A, SD2222AF, SQ2222A,  
 SQ2222AF, 2N5582, 2N6989, 2N6990

**Product Summary:**

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Features:** Medium power ratings

**Mechanical Specifications**

<b>Metallization</b>	Top	Al - 24 kÅ min.
	Backside	Au - 6.5 kÅ nom.
<b>Bonding Pad Size</b>	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
<b>Die Thickness</b>	8 mils nominal	
<b>Chip Area</b>	20 mils x 20 mils	
<b>Top Surface</b>	Silox Passivated	

**Electrical Characteristics**

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10\text{ mA}, I_B = 0$	40	---	V dc
$BV_{CBO}$	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	75	---	V dc
$BV_{EBO}$	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0	---	V dc
$I_{CBO}$	$V_{CB} = 50\text{ V}, I_E = 0$	---	10	nA dc
$h_{FE}$	$I_C = 150\text{ mA dc}, V_{CE} = 10\text{ V}$	100	300	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*